New Jersey Semi-Co	nducto	r Product	s, Inc.			
20 STERN AVE. SPRINGFIELD, NEW JERSEY 07081 U.S.A.						TELEPHONE: (973) 376-2922 (212) 227-6005 FAX: (973) 376-8960
Silico	n					(11)
011100	7. I.					
Power lab						
Transistor D40P						
FEATURING: • POWER-GLAS Passivation • High Free Air Power Dissipation • Hard Solder Mountdown • Fast Switching • Brown for NPN						Brown BC Leads can be formed to a TO-5 Pin Configuration.
absolute maximur	m ratir	ngs: (25°C unl	ess otherwise	specified)		
Voltages Collector to Emitter Emitter to Base Collector to Base Current Collector (Continous) Power Dissination	V <sub>CEO</sub> V <sub>EBO</sub> V <sub>CBO</sub> I <sub>c</sub>	<b>D40P1</b> 120 7 200	<b>D40P3</b> 180 7 250 0.5	<b>D40P5</b> 225 7 300	Volts Volts Volts Amp.	
Tab at 25°C Tab at 70°C Free Air at 50°C	$P_{T}$	۰			Watts Watts Watts	1981-1981. 1981-1981. 1981-1981. 1981-1981. 1981-1981. 1981-1981. 1981-1981. 1981-1981. 1981-1981. 1981-1981. 1981-1981. 1981-1981. 1981-1981. 1981-1981. 1981-1981. 1981.
Free Air at 50°C (without tab) Thermal Resistance Junction to Case Junction to Ambient (with tab) (without tab)	Rθjc Rθja	4	-20 $$		°C/W °C/W	An insulating hardware kit (mica washer, nylon shoulder washer, and solder lug) is available at an additional cost upon request. Kit #138B8189P11.
Temperature Operating Storage Lead Soldering, 1/16" ± 1/32"	$\substack{T_j\\T_{stg}}$	<u></u>	-55 to +150 -55 to +150		°C °C	Dimensional Outlines
From case for 10 sec. max.	TL	4	- +260		°C	
electrical charact	eristic	S: (25°C unless	otherwise spe	cified)		
Forward Current Transfer Rati $(I_C = 80 \text{ mA}, V_{CE} = 10V)$ $(I_C = 2 \text{ mA}, V_{CE} = 10V)$ Collector to Emitter Voltage	Forward Current Transfer Ratio ( $I_C = 80 \text{ mA}, V_{CE} = 10V$ ) ( $I_C = 2 \text{ mA}, V_{CE} = 10V$ ) Collector to Emitter Voltage ( $I_C = 1.0 \text{ mA}, I_b = 0$ ) p40P1 p40P3 p40P5			Min. 40 20	Max.	Units
$(I_{C} = 1.0 \text{ mA}, I_{b} = 0)$ D40P1 D40P3 D40P5				120 180 225		Volts Volts Volts
Collector Cutoff Current (Rated V <sub>CEO</sub> )		I <sub>CBO</sub>		_	10	μΑ
$(V_{EBO} = 7V)$		IEBO			10	μΑ
Collector Saturation Voltage $(I_C = 100 \text{ mA}, I_B = 10 \text{ mA})$	ollector Saturation Voltage ( $I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$ ) $V_{CE}$ (SAT		SAT)		1	Volt
Base Saturation Voltage ( $I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$ ) Gain Bandwidth Product		V <sub>BE</sub> (SAT)		-	1.5	Volt
$(I_C = 80 \text{ mA}, V_{CE} = 10\text{V})$ Storage Time		fT		50	-	MHz
$(I_C (ON) = 80 \text{ mA}, I_B (ON) = 8$ $I_B (OFF) =$	8 mA 8 mA)	ts			2.5	µsec
$(V_{CB} = 10V, I_E = 0)$		CCB		_	6	pf



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